

# Far UV Sensor

## GFUV-T10GD-L

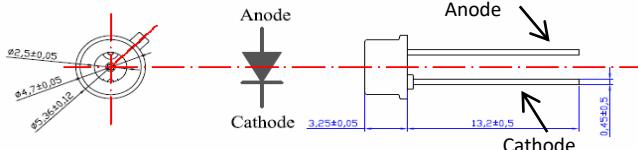


<b>Features</b>	Aluminium Gallium Nitride Based Material Schottky-type Photodiode Photovoltaic Mode Operation Good Solar Blindness
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<b>Applications</b>	<b>Far UV Monitoring</b> <b>Excimer Lamp Monitoring</b>
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### Outline Diagrams and Dimensions



### Absolute Maximum Ratings

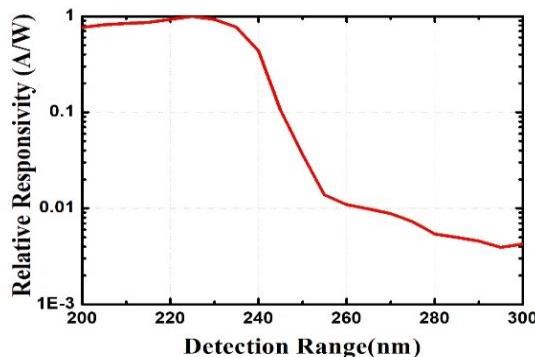
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T <sub>st</sub>	-40	90	°C	
Operating Temperature	T <sub>op</sub>	-30	85	°C	
Reverse Voltage	V <sub>r, max.</sub>		2	V	
Forward Current	I <sub>f,max.</sub>		1	mA	
Optical Source Power Range	P <sub>opt</sub>	0.1m	100m	W/cm <sup>2</sup>	Excimer Lamp
Soldering Temperature	T <sub>sol</sub>		260	°C	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100mW/cm<sup>2</sup>.

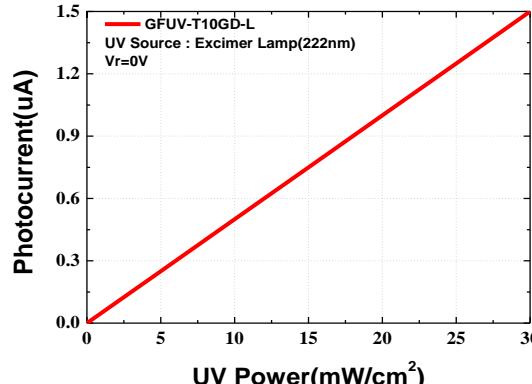
### Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I <sub>d</sub>			100	pA	V <sub>r</sub> = 1 V
Photo Current	I <sub>ph</sub>	45	50	55	nA	222nm peak FUV Lamp, 1mW/cm <sup>2</sup>
		2.12	2.35	2.58	nA	172nm peak VUV Lamp, 1mW/cm <sup>2</sup>
Spectral Detection range	λ			245	nm	
Active area			1.536		mm <sup>2</sup>	

### Relative Responsivity(A/W)



### Photocurrent along UV Power



### Caution

ESD can damage the device hence please avoid ESD. Insulate the cap of TO-CAN or it can cause malfunction of the device.